

Voltage modulation of interfacial Dzyaloshinskii-Moriya interaction on Fe|MgO

○縄岡 孝平¹、三輪 真嗣¹、塩田 陽一^{1,2}、野崎 隆行²、湯浅 新治²、水落 憲和¹、鈴木 義茂¹

(1 阪大院基礎工、2 産総研ナノスピ)

Kohei Nawaoka¹, Shinji Miwa¹, Yoichi Shiota^{1,2}, Takayuki Nozaki², Shinji Yuasa²,

Norikazu Mizuochi¹, Yoshishige Suzuki¹ (1 Osaka Univ., 2 AIST)

E-mail: nawaoka@spin.mp.es.osaka-u.ac.jp

Dzyaloshinskii-Moriya interaction (DMI) is an antisymmetric exchange interaction. The DMI changes magnetism drastically and is voltage controllable [1]. Up to now, this voltage modulation of DMI has been studied in multiferroic materials. Recently, interfacial DMI was reported in spin-wave research on W/Fe[2], but its voltage modulation has never been reported yet. In this research, we demonstrated the voltage modulation of interfacial DMI in spin wave devices.

Fe|MgO-based single crystalline multilayer was prepared by molecular beam epitaxy on MgO substrate. Figure 1 is the schematic image of a spin-wave device and measurement circuit. Two micro-antennae with vector network analyzer (VNA) were employed to generate and detect the spin-waves. By applying external magnetic field normal to the spin-wave propagation direction, magnetostatic surface spin-wave has been employed to characterize the voltage controlled magnetic anisotropy and interfacial DMI. Spin-wave signal was modulated by external voltage. We found that the voltage modulation was explained by the resonant frequency shift [3]. Figure 2 shows relation between their frequency shift of S_{21} (S_{12}) and external voltage as black (blue) circles. Their slopes were estimated to be $\delta f_{21}=0.032\pm0.01$ and $\delta f_{12}=0.028\pm0.01$ (MHz/V), respectively. The frequency shift can be mainly explained by voltage controlled magnetic anisotropy, in addition, the distinct difference between the δf_{21} and the δf_{12} shows the voltage controlled interfacial DMI at Fe|MgO. [3] In the presentation, the effect of the Pt-atomic-layer insertion at the Fe|MgO interface will be also discussed.

This work was funded by ImPACT Program and the Grant-in-Aid for Scientific Research (S).

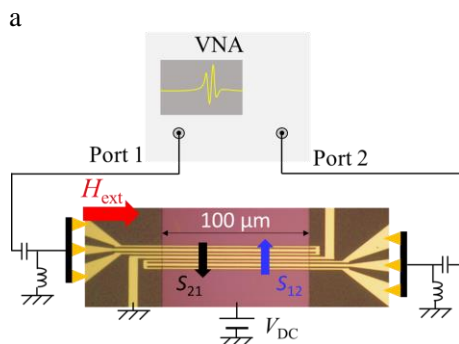


Figure 1 Measurement set up and spin-wave device

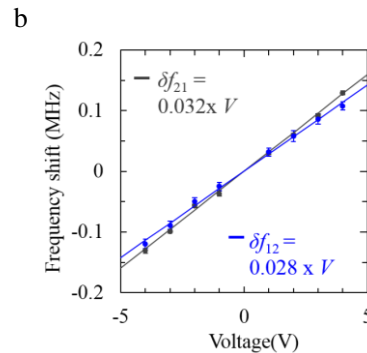


Figure 2 Voltage dependence of freq. shift

[1] H. Katsura, *et al.*, PRL. **95**, 057205 (2005).

[2] K. Zakeri, *et al.*, PRL. **104**, 137203 (2010).

[3] K. Nawaoka, *et al.*, APEX, **8**, 063004(2015) .